

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2794

DESCRIPTION

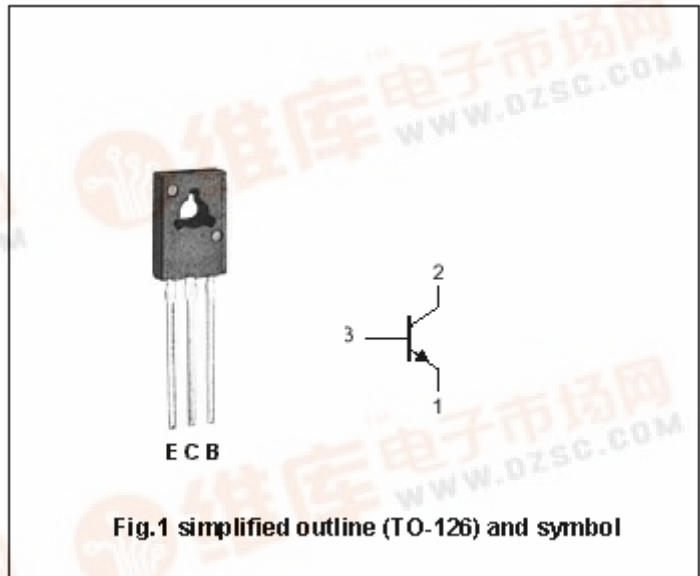
- With TO-126 package
- Low collector saturation voltage

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter -base voltage	Open collector	5	V
I _C	Collector current (DC)		2	A
I _{CM}	Collector current-Peak		6	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; I _B =0	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.6	V
V _{BE}	Base-emitter on voltage	I _C =1A; V _{CE} =2V			1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =60V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA
h _{FE-1}	DC current gain	I _C =150mA; V _{CE} =2V	50			
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =2V	25			
f _T	Transition frequency	I _C =100mA; V _{CE} =5V		40		MHz

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PACKAGE OUTLINE

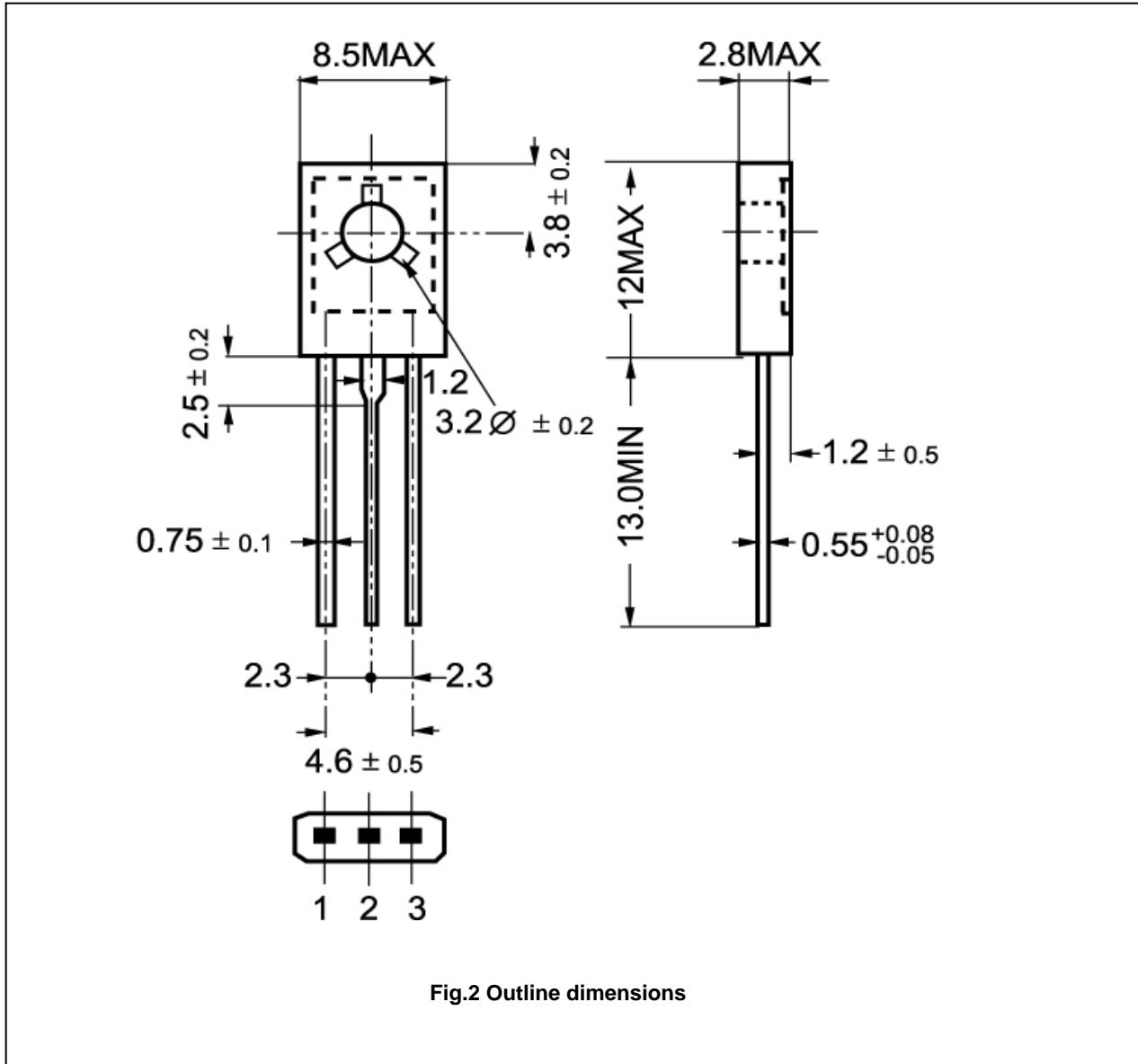


Fig.2 Outline dimensions